

ABSTRACT OF THE DISCLOSURE

Photoresist monomers of following Formula 1, photoresist polymers thereof, and photoresist compositions containing the same. The photoresist polymer includes a repeating unit comprising the photoresist monomer of Formula 1 as a comonomer and the photoresist composition containing the same have excellent etching resistance, heat resistance and adhesiveness to a wafer, and is developable in aqueous tetramethylammonium hydroxide (TMAH) solution. In addition, the photoresist composition has low light absorbance at 157nm wavelength, and thus is suitable for a photolithography process using ultraviolet light sources such as VUV (157nm) in fabricating a minute circuit for a high integration semiconductor device.

Formula 1

